

isc Silicon PNP Power Transistors

MJD45H11

DESCRIPTION

- Low Collector-Emitter Saturation Voltage
: $V_{CE(sat)} = 1.0V(Max) @ I_C = 8A$
- Fast Switching Speeds
- Complement to Type MJD44H11
- DPAK for Surface Mount Applications
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

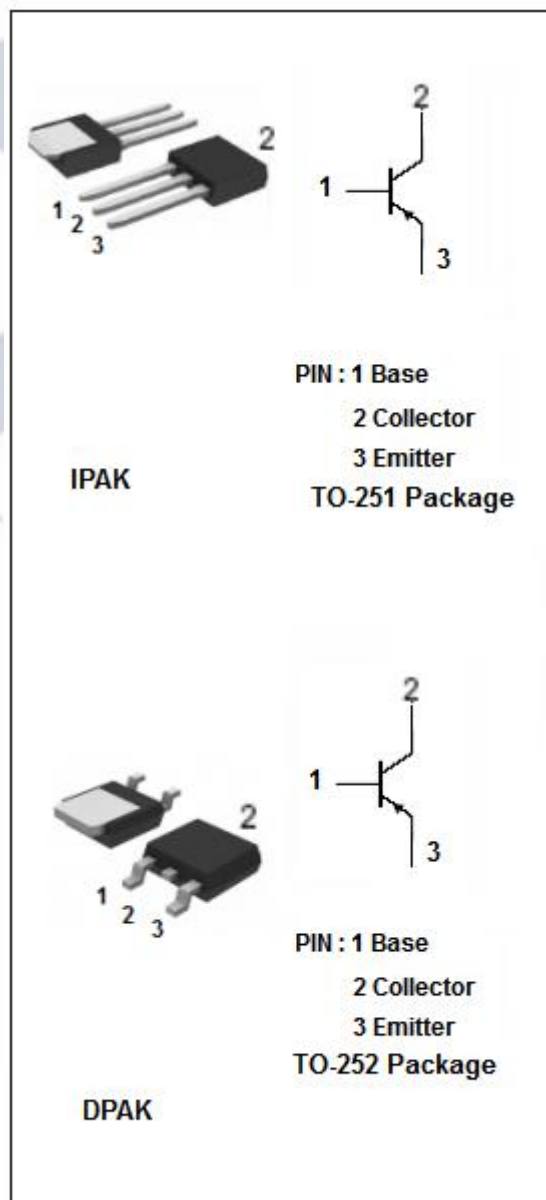
- Designed for general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifier.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-8	A
I_{CM}	Collector Current-Peak	-16	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	20	W
	Collector Power Dissipation @ $T_a=25^{\circ}C$	1.75	
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	6.25	$^{\circ}C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	71.4	$^{\circ}C/W$



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ELECTRICAL CHARACTERISTICS

 $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -30\text{mA}; I_B = 0$	-80		V	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -8\text{A}; I_B = -0.4\text{A}$			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -8\text{A}; I_B = -0.8\text{A}$			-1.5	V
I_{CES}	Collector Cutoff Current	$V_{CE} = \text{Rated } V_{CEO}; V_{BE} = 0$			-1.0	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-1.0	μA
h_{FE-1}	DC Current Gain	$I_C = -2\text{A}; V_{CE} = -1\text{V}$	60			
h_{FE-2}	DC Current Gain	$I_C = -4\text{A}; V_{CE} = -1\text{V}$	40			
C_{OB}	Output Capacitance	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}$		130		pF
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -10\text{V}; f_{test} = 20\text{MHz}$		40		MHz

Switching Times; Resistive Load

$t_d + t_r$	Delay and Rise Time			135		ns
t_s	Storage Time	$I_C = -5\text{A}; I_{B1} = I_{B2} = -0.5\text{A}$		500		ns
t_f	Fall Time			100		ns

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Outline Drawing

